

Specification Tentative	Products MOSFET	Type 2SK2102
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1. TYPE. 2SK2102
2. DESCRIPTION. Silicon N-Channel MOS FET.
3. APPLICATION. Switching.
4. ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current	I _D	200	mA
Power Dissipation	P _D	200	mW
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55~150	°C

5. ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Gate-Source Leak Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0V	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	10	μA
Gate Threshold Voltage	V _{GS(off)}	I _D = 1mA, V _{DS} = 10V	0.5	-	1.8	V
Forward Transfer Admittance	Y _{fs}	I _D = 0.1A, V _{DS} = 10V	50	-	-	mS
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D = 0.1A, V _{GS} = 10V	-	-	2.0	Ω
Input Capacitance	C _{iss}	V _{DS} = 10V	-	30	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0V	-	15	-	pF
Reverse Transfer Capacitance	C _{rss}	f = 1MHz	-	10	-	pF
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15V, R _{in} = 10Ω	-	15	-	ns
Rise Time	t _r	R _L = 150Ω	-	25	-	ns
Turn-Off Delay Time	t _{d(off)}	V _{GS} = 10V	-	80	-	ns
Fall Time	t _f	I _D = 0.1A	-	300	-	ns

ROHM CO., LTD.

Design

Approval

Specification No.

TKK2102-1

Date

Jan 12/93

J. Honishi

Specification

Products

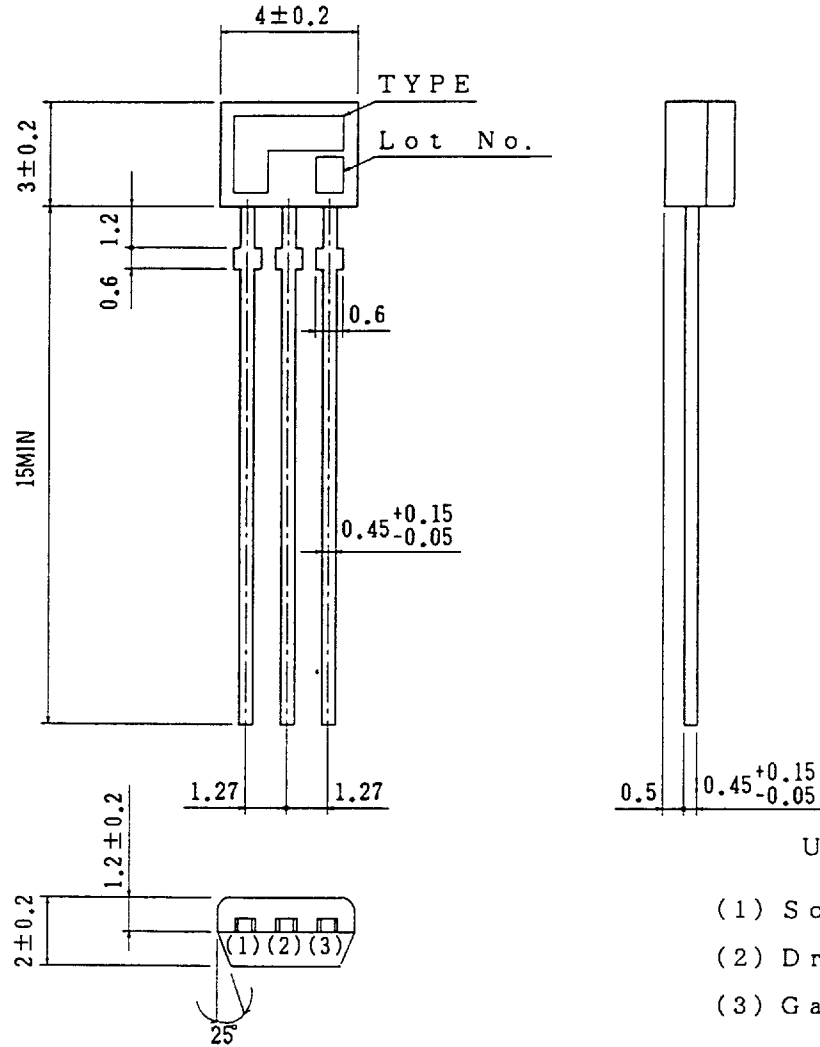
SPT

Type

2SK2102

Figure 1.

FD:fig-8420



UNIT : mm

- (1) Source
- (2) Drain
- (3) Gate

A factory

APOLLO ELECTRONICS CO.,LTD.

883 Kamikitajima,Chikugo,Fukuoka 833, Japan

The net weight

0.13 g / p c e

Two kind of marking are available

- Direct Laser Marking
- Laser Marking on silver color under coated surface

※Minimum order quantity for Bulk Packing:2,000pcs/INNER CASE

ROHM CO., LTD.

Date

Jan 12 93